

# 1310nm InGaAs 3000um PD Chip datasheet

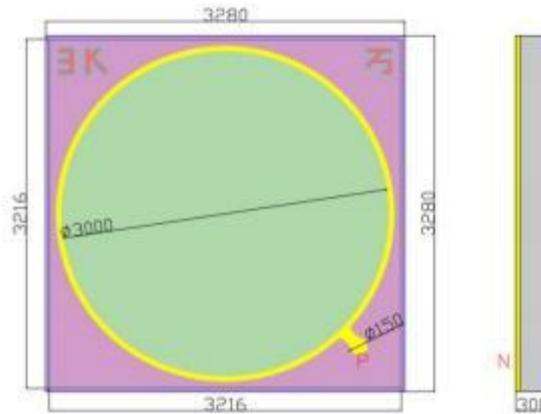
P/N : WIMA-3000

## Application

Optical sensor  
Optical power meter

## Structure

InGaAs / InP PIN Chip  
P Electrode (anode) : Gold  
N Electrode (cathode) : Gold



## DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	-	3000	-	μm
Chip width	3230	3280	3330	μm
Chip length	3230	3280	3330	μm
Chip height	280	300	320	μm
Pad Area	140	150	160	μm

## Electro-Optical Characteristics ( @ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	Id	Vr=-1V	-	15	75	nA
Capacitance	Cp	Vr=-1V	-	1000	-	pF
Reverse Breakdown	Vbr	Ir=-10μA	20	38	60	V
Responsivity	R	@1310 nm	0.8	0.9	-	A/W
Wavelength range	λ		900	1310	1600	nm

PS. ESD ( HBM ) > 800V

## ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 125°C
Forward Current	10mA